

Title (en)

HIGHLY OXYGEN-SENSITIVE SILICON LAYER AND METHOD FOR OBTAINING SAME

Title (de)

HOCHSAUERSTOFFEMPFLINDLICHE SILIZIUMSCHICHT UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)

COUCHE DE SILICIUM TRES SENSIBLE A L'OXYGENE ET PROCEDE D'OBTENTION DE CETTE COUCHE

Publication

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Application

**EP 06764054 A 20060704**

Priority

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Abstract (en)

[origin: WO2007003638A1] The invention concerns a highly oxygen-sensitive silicon layer and a method for obtaining same. Said layer (2), formed on a substrate (4) for example made of SiC, has a 3x2 structure. The method for obtaining same consists in depositing silicon substantially uniformly on one surface of the substrate. The invention is applicable for example in microelectronics.

IPC 8 full level

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